

Tarni Aggarwal

List of Publications by Year in descending order

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14
papers

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1478505

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49
citing authors

#	ARTICLE	IF	CITATIONS
1	Reduced Auger Coefficient through Efficient Carrier Capture and Improved Radiative Efficiency from the Broadband Optical Cavity: A Mechanism for Potential Droop Mitigation in InGaN/GaN LEDs. ACS Applied Materials & Interfaces, 2022, 14, 13812-13819.	8.0	3
2	Carrier-Induced Defect Saturation in Green InGaN LEDs: A Potential Phenomenon to Enhance Efficiency at Higher Wavelength Regime. ACS Photonics, 2021, 8, 926-932.	6.6	13
3	Carrier Recovery from Sub-Bandgap States in a GaN-Based Quantum-Confined Structure: Identification of Carrier Reservoirs through Femtosecond Pump-Probe Spectroscopy. Journal of Physical Chemistry C, 2021, 125, 3535-3541.	3.1	5
4	Investigation of Ultrafast Carrier Dynamics in InGaN/GaN-Based Nanostructures Using Femtosecond Pump-Probe Absorption Spectroscopy. Physica Status Solidi (B): Basic Research, 2021, 258, 2100223.	1.5	3
5	Gradual Carrier Filling Effect in "Green" InGaN/GaN Quantum Dots: Femtosecond Carrier Kinetics with Sequential Two-Photon Absorption. ACS Applied Materials & Interfaces, 2021, 13, 45033-45039.	8.0	2
6	Determining the carrier decay kinetics in QCSE-exhibiting materials: An accurate interpretation of transient absorption spectroscopy data. , 2021, , .		1
7	Carrier De-trapping from the Sub-bandgap States: A novel mechanism in InGaN/GaN systems manifested by ultrafast pump-probe spectroscopy. , 2021, , .		0
8	Femto-Second Carrier and Photon Dynamics in Site Controlled Hexagonal InGaN/GaN Isolated Quantum Dots: Natural Radial Potential Well and Its Dynamic Modulation. ACS Photonics, 2020, 7, 2555-2561.	6.6	6
9	Role of defect saturation in improving optical response from InGaN nanowires in higher wavelength regime. Nanotechnology, 2020, 31, 495705.	2.6	11
10	Impact of distributed Bragg reflector on carrier and photon dynamics in GaN-based surface emitting diodes manifested by ultrafast transient absorption spectroscopy. Japanese Journal of Applied Physics, 2019, 58, SCCC15.	1.5	6
11	Theoretical modelling of exciton binding energy, steady-state and transient optical response of GaN/InGaN/GaN and AlGaN/GaN/AlGaN core-shell nanostructures. Nanotechnology, 2019, 30, 274002.	2.6	10
12	Enhanced luminescence from InGaN/GaN nano-disk in a wire array caused by surface potential modulation during wet treatment. Nanotechnology, 2019, 30, 104001.	2.6	6
13	Engineering V-shaped pits in InGaN layers grown by PA-MBE toward optimizing the active region of green LEDs. Journal of the Optical Society of America B: Optical Physics, 2019, 36, 616.	2.1	10
14	Determination of strain relaxation in InGaN/GaN nanowalls from quantum confinement and exciton binding energy dependent photoluminescence peak. Scientific Reports, 2018, 8, 8404.	3.3	10